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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

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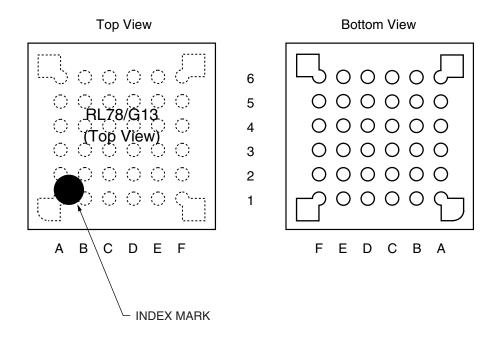
Details	
Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	48
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 12x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LFQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f100ledfb-30

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

1.3.6 36-pin products

• 36-pin plastic WFLGA (4 × 4 mm, 0.5 mm pitch)



	А	В	С	D	E	F	_
	P60/SCLA0	Vdd	P121/X1	P122/X2/EXCLK	P137/INTP0	P40/TOOL0	
6							6
	P62	P61/SDAA0	Vss	REGC	RESET	P120/ANI19	
5							5
4	P72/SO21	P71/SI21/ SDA21	P14/RxD2/SI20/ SDA20/(SCLA0) /(TI03)/(TO03)	P31/TI03/TO03/ INTP4/ PCLBUZ0	P00/TI00/TxD1	P01/TO00/RxD1	4
3	P50/INTP1/ SI11/SDA11	P70/SCK21/ SCL21	P15/PCLBUZ1/ SCK20/SCL20/ (TI02)/(TO02)	P22/ANI2	P20/ANI0/ AVrefp	P21/ANI1/ AVREFM	3
2	P30/INTP3/ SCK11/SCL11	P16/TI01/TO01/ INTP5/(RxD0)	P12/SO00/ TxD0/TOOLTxD /(TI05)/(TO05)	P11/SI00/RxD0/ TOOLRxD/ SDA00/(TI06)/ (TO06)	P24/ANI4	P23/ANI3	2
1	P51/INTP2/ SO11	P17/TI02/TO02/ (TxD0)	P13/TxD2/ SO20/(SDAA0)/ (TI04)/(TO04)	P10/SCK00/ SCL00/(TI07)/ (TO07)	P147/ANI18	P25/ANI5	1
	А	В	С	D	E	F	

Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

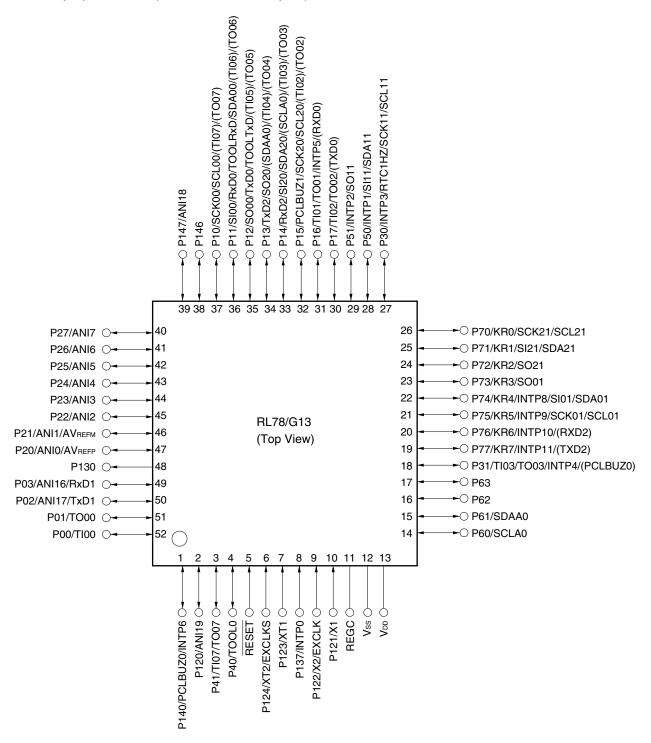
Remarks 1. For pin identification, see 1.4 Pin Identification.

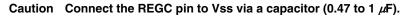
Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.



1.3.10 52-pin products

• 52-pin plastic LQFP (10 × 10 mm, 0.65 mm pitch)





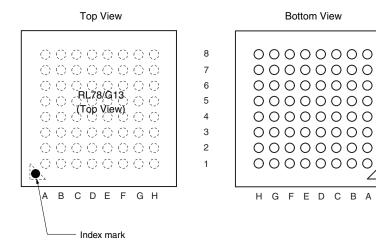
Remarks 1. For pin identification, see 1.4 Pin Identification.

Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.



Bottom View

• 64-pin plastic VFBGA (4 × 4 mm, 0.4 mm pitch)



Pin No.	Name	Pin No.	Name	Pin No.	Name	Pin No.	Name
A1	P05/TI05/TO05	C1	P51/INTP2/SO11	E1	P13/TxD2/SO20/ (SDAA0)/(TI04)/(TO04)	G1	P146
A2	P30/INTP3/RTC1HZ /SCK11/SCL11	C2	P71/KR1/SI21/SDA21	E2	P14/RxD2/SI20/SDA20 /(SCLA0)/(TI03)/(TO03)	G2	P25/ANI5
A3	P70/KR0/SCK21 /SCL21	СЗ	P74/KR4/INTP8/SI01 /SDA01	E3	P15/SCK20/SCL20/ (TI02)/(TO02)	G3	P24/ANI4
A4	P75/KR5/INTP9 /SCK01/SCL01	C4	P52/(INTP10)	E4	P16/TI01/TO01/INTP5 /(SI00)/(RxD0)	G4	P22/ANI2
A5	P77/KR7/INTP11/ (TxD2)	C5	P53/(INTP11)	E5	P03/ANI16/SI10/RxD1 /SDA10	G5	P130
A6	P61/SDAA0	C6	P63	E6	P41/TI07/TO07	G6	P02/ANI17/SO10/TxD1
A7	P60/SCLA0	C7	Vss	E7	RESET	G7	P00/TI00
A8	EVDD0	C8	P121/X1	E8	P137/INTP0	G8	P124/XT2/EXCLKS
B1	P50/INTP1/SI11 /SDA11	D1	P55/(PCLBUZ1)/ (SCK00)	F1	P10/SCK00/SCL00/ (TI07)/(TO07)	H1	P147/ANI18
B2	P72/KR2/SO21	D2	P06/TI06/TO06	F2	P11/SI00/RxD0 /TOOLRxD/SDA00/ (TI06)/(TO06)	H2	P27/ANI7
В3	P73/KR3/SO01	D3	P17/TI02/TO02/ (SO00)/(TxD0)	F3	P12/SO00/TxD0 /TOOLTxD/(INTP5)/ (TI05)/(TO05)	H3	P26/ANI6
B4	P76/KR6/INTP10/ (RxD2)	D4	P54	F4	P21/ANI1/AVREFM	H4	P23/ANI3
B5	P31/TI03/TO03 /INTP4/(PCLBUZ0)	D5	P42/TI04/TO04	F5	P04/SCK10/SCL10	H5	P20/ANI0/AVREFP
B6	P62	D6	P40/TOOL0	F6	P43	H6	P141/PCLBUZ1/INTP7
B7	Vdd	D7	REGC	F7	P01/TO00	H7	P140/PCLBUZ0/INTP6
B8	EVsso	D8	P122/X2/EXCLK	F8	P123/XT1	H8	P120/ANI19

Cautions 1. Make EVsso pin the same potential as Vss pin.

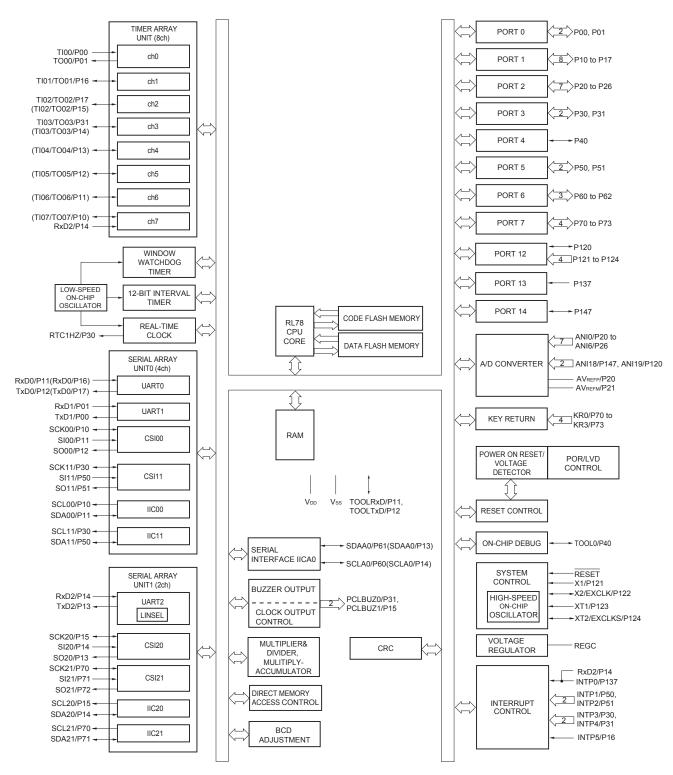
- 2. Make VDD pin the potential that is higher than EVDD0 pin.
- 3. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

- 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the VDD and EVDD0 pins and connect the Vss and EVss0 pins to separate ground lines.
- 3. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.



1.5.7 40-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.

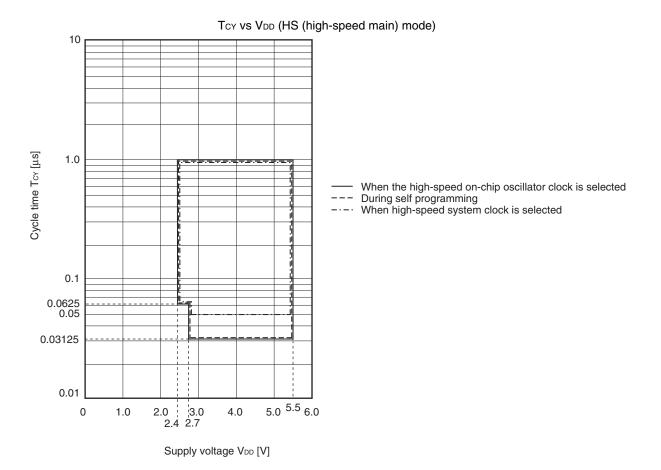


NoteThe following conditions are required for low voltage interface when $E_{VDD0} < V_{DD}$ $1.8 V \le EV_{DD0} < 2.7 V : MIN. 125 ns$ $1.6 V \le EV_{DD0} < 1.8 V : MIN. 250 ns$

 $\label{eq:rescaled} \textbf{Remark} \quad \text{f_{MCK}: Timer array unit operation clock frequency}$

(Operation clock to be set by the CKSmn0, CKSmn1 bits of timer mode register mn (TMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0 to 7))

Minimum Instruction Execution Time during Main System Clock Operation



R01DS0131EJ0330 Rev.3.30 Mar 31, 2016



(2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)

Parameter	Symbol	Conditions		、 U	h-speed Mode	``	/-speed Mode	LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkCY1	tксү1 \geq 2/fclк	$4.0~V \leq EV_{\text{DD0}} \leq 5.5~V$	62.5		250		500		ns
			$2.7~V \leq EV_{\text{DD0}} \leq 5.5~V$	83.3		250		500		ns
SCKp high-/low-level width	tĸнı, tĸ∟ı	$4.0 V \le EV_{DI}$	$1.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$ the			tксү1/2 – 50		tксү1/2 – 50		ns
		$2.7~V \leq EV_{DD0} \leq 5.5~V$		tксү1/2 – 10		tксү1/2 – 50		tксү1/2 – 50		ns
SIp setup time (to SCKp [↑])	tsik1	$4.0 \ V \le EV_{DI}$	$00 \leq 5.5 \text{ V}$	23		110		110		ns
Note 1		$2.7 \text{ V} \leq EV_{\text{DI}}$	$00 \leq 5.5 \text{ V}$	33		110		110		ns
Slp hold time (from SCKp↑) ^{Note 2}	tksii	$2.7~V \leq EV_{\text{DD0}} \leq 5.5~V$		10		10		10		ns
Delay time from SCKp↓ to SOp output ^{Note 3}	tkso1	C = 20 pF ^{Not}	te 4		10		10		10	ns

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.7 \text{ V} \le \text{EV}_{\text{DD}} = \text{EV}_{\text{DD}} \le 5.5 \text{ V}, \text{ Vss} = \text{EV}_{\text{SS}} = \text{EV}_{\text{SS}} = 0 \text{ V})$

- **Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to $SCKp\downarrow$ " when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **3.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp[↑]" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- **Remarks 1.** This value is valid only when CSI00's peripheral I/O redirect function is not used.
 - p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0),
 g: PIM and POM numbers (g = 1)
 - 3. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00))



Remarks 1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3),

g: PIM and POM numbers (g = 0, 1, 4, 5, 8, 14)

2. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

(4) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) (1/2) ($T_A = -40$ to $+85^{\circ}$ C, 1.6 V \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 V, Vss = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Condit	ions		h-speed Mode		/-speed Mode		-voltage Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkCY2	$4.0~V \leq EV_{DD0} \leq 5.5$	20 MHz < fмск	8/fмск		_		_		ns
Note 5		V	fмск \leq 20 MHz	6/fмск		6/fмск		6/fмск		ns
		$2.7~V \leq EV_{\text{DD0}} \leq 5.5$	16 MHz < fмск	8/fмск		_		_		ns
		V	fмск \leq 16 MHz	6/fмск		6/fмск		6/fмск		ns
		$2.4 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$		6/fмск and 500		6/fмск and 500		6/fмск and 500		ns
		$1.8~V \le EV_{DD0} \le 5.5~V$		6/fмск and 750		6/fмск and 750		6/fмск and 750		ns
		$1.7~V \leq EV_{DD0} \leq 5.5~V$		6/fмск and 1500		6/fмск and 1500		6/fмск and 1500		ns
		$1.6 \ V \leq EV_{\text{DD0}} \leq 5.5$	V	—		6/fмск and 1500		6/fмск and 1500		ns
SCKp high-/low- level width	tкн2, tкL2	$4.0~V \le EV_{DD0} \le 5.5~V$		tксү2/2 – 7		tксү2/2 - 7		tксү2/2 - 7		ns
		$2.7~V \leq EV_{DD0} \leq 5.5~V$		tксү2/2 – 8		tксү2/2 - 8		tксү2/2 - 8		ns
		$1.8~V \le EV_{DD0} \le 5.5~V$		tксү2/2 – 18		tксү2/2 – 18		tксү2/2 – 18		ns
	$1.7~V \leq EV_{DD0} \leq 5.5~V$			tксү2/2 – 66		tксү2/2 - 66		tксү2/2 - 66		ns
		$1.6~V \leq EV_{\text{DD0}} \leq 5.5~V$		_		tксү2/2 - 66		tксү2/2 - 66		ns

(Notes, Caution, and Remarks are listed on the next page.)



Parameter	Symbol	Conditions	、 U	h-speed Mode	``	/-speed Mode	`	-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Data setup time (reception)	tsu:dat	$\label{eq:constraint} \begin{array}{l} 2.7~V \leq EV_{\text{DD0}} \leq 5.5~V, \\ C_{\text{b}} = 50~pF,~R_{\text{b}} = 2.7~k\Omega \end{array}$	1/fмск + 85 _{Note2}		1/fмск + 145 _{Note2}		1/fмск + 145 _{Note2}		ns
		$\label{eq:linear} \begin{split} 1.8 \ V &\leq EV_{\text{DD0}} \leq 5.5 \ V, \\ C_{\text{b}} &= 100 \ p\text{F}, \ R_{\text{b}} = 3 \ k\Omega \end{split}$	1/fмск + 145 _{Note2}		1/fмск + 145 _{Note2}		1/fмск + 145 _{Note2}		ns
		$\label{eq:linear} \begin{split} 1.8 \ V &\leq EV_{\text{DD0}} < 2.7 \ V, \\ C_{\text{b}} &= 100 \ p\text{F}, \ R_{\text{b}} = 5 \ k\Omega \end{split}$	1/fмск + 230 _{Note2}		1/f _{MCK} + 230 _{Note2}		1/fмск + 230 _{Note2}		ns
		$\label{eq:linear} \begin{array}{l} 1.7 \mbox{ V} \leq EV_{\mbox{\tiny DD0}} < 1.8 \mbox{ V}, \\ C_{\mbox{\tiny b}} = 100 \mbox{ pF}, \mbox{ R}_{\mbox{\tiny b}} = 5 \mbox{ k}\Omega \end{array}$	1/fмск + 290 _{Note2}		1/f _{MCK} + 290 _{Note2}		1/fмск + 290 _{Note2}		ns
		$\label{eq:linear} \begin{array}{l} 1.6 \mbox{ V} \leq EV_{\mbox{DD0}} < 1.8 \mbox{ V}, \\ C_{\mbox{\tiny b}} = 100 \mbox{ pF}, \mbox{ R}_{\mbox{\tiny b}} = 5 k\Omega \end{array}$	—		1/f _{MCK} + 290 _{Note2}		1/fмск + 290 _{Note2}		ns
Data hold time (transmission)	thd:dat	$\begin{array}{l} 2.7 \ \text{V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \ \text{V}, \\ \text{C}_{\text{b}} = 50 \ \text{pF}, \ \text{R}_{\text{b}} = 2.7 \ \text{k}\Omega \end{array}$	0	305	0	305	0	305	ns
		$\label{eq:linear} \begin{array}{l} 1.8 \mbox{ V} \leq EV_{\mbox{DD0}} \leq 5.5 \mbox{ V}, \\ C_{\mbox{\tiny b}} = 100 \mbox{ pF}, \mbox{ R}_{\mbox{\tiny b}} = 3 k\Omega \end{array}$	0	355	0	355	0	355	ns
		$\label{eq:linear} \begin{array}{l} 1.8 \mbox{ V} \leq EV_{\mbox{DD0}} < 2.7 \mbox{ V}, \\ C_{\mbox{\tiny b}} = 100 \mbox{ pF}, \mbox{ R}_{\mbox{\tiny b}} = 5 k\Omega \end{array}$	0	405	0	405	0	405	ns
		$1.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 1.8 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 5 \text{ k}\Omega$	0	405	0	405	0	405	ns
		$1.6 \text{ V} \leq \text{EV}_{\text{DD0}} < 1.8 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 5 \text{ k}\Omega$	_	_	0	405	0	405	ns

(5)	During communication at same potential (simplified I ² C mode) (2/2)
	$(T_{A} = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Notes 1. The value must also be equal to or less than $f_{MCK}/4$.

2. Set the fMCK value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the normal input buffer and the N-ch open drain output (VDD tolerance (When 20- to 52-pin products)/EVDD tolerance (When 64- to 128-pin products)) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

(**Remarks** are listed on the next page.)



(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (1/3)

Parameter	Symbol		Conditions	HS (hig	h-speed Mode	LS (low		`	-voltage Mode	Unit	
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
SCKp cycle time	t ксү1	tксү1 ≥ 4/fc∟к	$\begin{array}{l} 4.0 \ V \leq EV_{\text{DD0}} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V, \\ C_b = 30 \ pF, \ R_b = 1.4 \ k\Omega \end{array}$	300		1150		1150		ns	
			$\begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	500		1150		1150		ns	
			$\begin{array}{l} 1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V^{\text{Note}}, \end{array}$	1150		1150		1150		ns	
SCKp high-level width	2.7 V C _b = 3 2.7 V 2.3 V C _b = 3 1.8 V 1.6 V	$2.7~V \leq V_b \leq 4.0~V,$		tксү1/2 – 75		tксү1/2 – 75		tксү1/2 – 75		ns	
			$C_b = 30 \text{ pF},$ 2.7 V $\leq EV_{DI}$ 2.3 V $\leq V_b \leq$ $C_b = 30 \text{ pF},$	₂₀ < 4.0 V, 2.7 V,	tксү1/2 – 170		tксү1/2 – 170		tксү1/2 – 170		ns
		$\label{eq:VDD} \begin{array}{l} 1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V^{\text{Note}}, \\ C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$		tксү1/2 – 458		tксү1/2 – 458		tксү1/2 – 458		ns	
SCKp low-level width	tĸ∟ı	$\begin{array}{l} 4.0 \ V \leq EV_{DI} \\ 2.7 \ V \leq V_b \leq \end{array}$	∞ ≤ 5.5 V, 4.0 V,	tксү1/2 – 12		tксү1/2 – 50		tксү1/2 – 50		ns	
		$\begin{split} C_b &= 30 \text{ pF}, \ R_b = 1.4 \text{ k}\Omega \\ \\ 2.7 \text{ V} &\leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}, \\ \\ 2.3 \text{ V} &\leq \text{V}_b \leq 2.7 \text{ V}, \end{split}$		tксү1/2 – 18		tксү1/2 – 50		tксү1/2 – 50		ns	
		$\label{eq:cb} \begin{array}{l} C_{\rm b} = 30 \mbox{ pF}, \\ \\ 1.8 \mbox{ V} \leq EV_{\rm DI} \\ 1.6 \mbox{ V} \leq V_{\rm b} \leq \\ \\ C_{\rm b} = 30 \mbox{ pF}, \end{array}$	⁰⁰ < 3.3 V, 2.0 V ^{Note} ,	tксү1/2 – 50		tксү1/2 – 50		tксү1/2 – 50		ns	

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Note Use it with $EV_{DD0} \ge V_b$.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (When 20- to 52-pin products)/EVDD tolerance (When 64- to 128-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed two pages after the next page.)



(4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AV_{REFM}/ANI1 (ADREFM = 1), target pin : ANI0, ANI2 to ANI14, ANI16 to ANI26

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}, \text{ Reference voltage (+)} = \text{V}_{BGR}^{\text{Note 3}}, \text{ Reference voltage (-)} = \text{AV}_{REFM} = 0 \text{ V}^{\text{Note 4}}, \text{HS (high-speed main) mode}$

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES				8		bit
Conversion time	t CONV	8-bit resolution	$2.4~V \leq V \text{DD} \leq 5.5~V$	17		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	8-bit resolution	$2.4~V \leq V \text{DD} \leq 5.5~V$			±0.60	%FSR
Integral linearity error ^{Note 1}	ILE	8-bit resolution	$2.4~V \leq V \text{DD} \leq 5.5~V$			±2.0	LSB
Differential linearity error Note 1	DLE	8-bit resolution	$2.4~V \leq V \text{DD} \leq 5.5~V$			±1.0	LSB
Analog input voltage	VAIN			0		$V_{\text{BGR}}{}^{\text{Note 3}}$	V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- 3. Refer to 2.6.2 Temperature sensor/internal reference voltage characteristics.

4. When reference voltage (-) = Vss, the MAX. values are as follows.

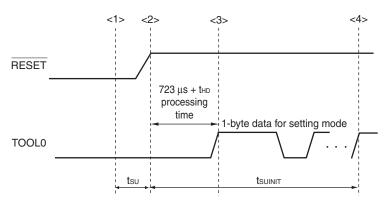
Zero-scale error: Add $\pm 0.35\%$ FSR to the MAX. value when reference voltage (–) = AV_{REFM}. Integral linearity error: Add ± 0.5 LSB to the MAX. value when reference voltage (–) = AV_{REFM}. Differential linearity error: Add ± 0.2 LSB to the MAX. value when reference voltage (–) = AV_{REFM}.



2.10 Timing of Entry to Flash Memory Programming Modes

$(T_{\text{A}} = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \leq \text{EV}_{\text{DD}} = \text{EV}_{\text{DD}} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Time to complete the communication for the initial setting after the external reset is released	tsuinit	POR and LVD reset must be released before the external reset is released.			100	ms
Time to release the external reset after the TOOL0 pin is set to the low level	ts∪	POR and LVD reset must be released before the external reset is released.	10			μs
Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)	tно	POR and LVD reset must be released before the external reset is released.	1			ms



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset is released (POR and LVD reset must be released before the external reset is released.).
- <3> The TOOL0 pin is set to the high level.
- <4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.
- **Remark** tsuinit: Communication for the initial setting must be completed within 100 ms after the external reset is released during this period.
 - $t_{su:}$ Time to release the external reset after the TOOL0 pin is set to the low level
 - thd: Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)



3. ELECTRICAL SPECIFICATIONS (G: INDUSTRIAL APPLICATIONS $T_A = -40$ to +105°C)

This chapter describes the following electrical specifications.

Target products G: Industrial applications $T_A = -40$ to $+105^{\circ}C$ R5F100xxGxx

- Cautions 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
 - 2. With products not provided with an EVDD0, EVDD1, EVSS0, or EVSS1 pin, replace EVDD0 and EVDD1 with VDD, or replace EVSS0 and EVSS1 with VSS.
 - 3. The pins mounted depend on the product. Refer to 2.1 Port Function to 2.2.1 Functions for each product.
 - 4. Please contact Renesas Electronics sales office for derating of operation under $T_A = +85^{\circ}C$ to +105°C. Derating is the systematic reduction of load for the sake of improved reliability.

Remark When RL78/G13 is used in the range of $T_A = -40$ to +85°C, see **CHAPTER 2 ELECTRICAL SPECIFICATIONS (T_A = -40 to +85°C)**.

There are following differences between the products "G: Industrial applications ($T_A = -40$ to $+105^{\circ}C$)" and the products "A: Consumer applications, and D: Industrial applications".

Parameter	Ар	pplication
	A: Consumer applications, D: Industrial applications	G: Industrial applications
Operating ambient temperature	T _A = -40 to +85°C	T _A = -40 to +105°C
Operating mode Operating voltage range	$\begin{array}{l} \text{HS (high-speed main) mode:} \\ \text{2.7 V} \leq V_{\text{DD}} \leq 5.5 \ \text{V@1 MHz to 32 MHz} \\ \text{2.4 V} \leq V_{\text{DD}} \leq 5.5 \ \text{V@1 MHz to 16 MHz} \\ \text{LS (low-speed main) mode:} \\ \text{1.8 V} \leq V_{\text{DD}} \leq 5.5 \ \text{V@1 MHz to 8 MHz} \\ \text{LV (low-voltage main) mode:} \\ \text{1.6 V} \leq V_{\text{DD}} \leq 5.5 \ \text{V@1 MHz to 4 MHz} \end{array}$	HS (high-speed main) mode only: 2.7 V \leq V _{DD} \leq 5.5 V@1 MHz to 32 MHz 2.4 V \leq V _{DD} \leq 5.5 V@1 MHz to 16 MHz
High-speed on-chip oscillator clock accuracy	$\begin{array}{l} 1.8 \ V \leq V_{DD} \leq 5.5 \ V \\ \pm 1.0\% @ \ T_{A} = -20 \ to \ +85^{\circ}C \\ \pm 1.5\% @ \ T_{A} = -40 \ to \ -20^{\circ}C \\ 1.6 \ V \leq V_{DD} < 1.8 \ V \\ \pm 5.0\% @ \ T_{A} = -20 \ to \ +85^{\circ}C \\ \pm 5.5\% @ \ T_{A} = -40 \ to \ -20^{\circ}C \end{array}$	$\begin{array}{l} 2.4 \ V \leq V_{DD} \leq 5.5 \ V \\ \pm 2.0\% @ \ T_{A} = +85 \ to \ +105^{\circ}C \\ \pm 1.0\% @ \ T_{A} = -20 \ to \ +85^{\circ}C \\ \pm 1.5\% @ \ T_{A} = -40 \ to \ -20^{\circ}C \end{array}$
Serial array unit	UART CSI: fcLk/2 (supporting 16 Mbps), fcLk/4 Simplified I ² C communication	UART CSI: fcLk/4 Simplified I ² C communication
IICA	Normal mode Fast mode Fast mode plus	Normal mode Fast mode
Voltage detector	Rise detection voltage: 1.67 V to 4.06 V (14 levels) Fall detection voltage: 1.63 V to 3.98 V (14 levels)	Rise detection voltage: 2.61 V to 4.06 V (8 levels) Fall detection voltage: 2.55 V to 3.98 V (8 levels)

(Remark is listed on the next page.)



3.2 Oscillator Characteristics

3.2.1 X1, XT1 oscillator characteristics

 $(T_A = -40 \text{ to } +105^{\circ}C, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation	Ceramic resonator/	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	1.0		20.0	MHz
frequency (fx) ^{Note}	crystal resonator	$2.4~V \leq V_{\text{DD}} < 2.7~V$	1.0		16.0	MHz
XT1 clock oscillation frequency (fx) ^{Note}	Crystal resonator		32	32.768	35	kHz

- **Note** Indicates only permissible oscillator frequency ranges. Refer to AC Characteristics for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.
- Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.
- **Remark** When using the X1 oscillator and XT1 oscillator, refer to **5.4 System Clock Oscillator**.

3.2.2 On-chip oscillator characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = 0 \text{ V})$

Oscillators	Parameters	Conditions			TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency ^{Notes 1, 2}	fін			1		32	MHz
High-speed on-chip oscillator		–20 to +85 °C	$2.4~V \leq V_{\text{DD}} \leq 5.5~V$	-1.0		+1.0	%
clock frequency accuracy		–40 to –20 °C	$2.4~V \leq V_{\text{DD}} \leq 5.5~V$	-1.5		+1.5	%
		+85 to +105 °C	$2.4~V \leq V_{\text{DD}} \leq 5.5~V$	-2.0		+2.0	%
Low-speed on-chip oscillator clock frequency	fı∟				15		kHz
Low-speed on-chip oscillator clock frequency accuracy				-15		+15	%

Notes 1. High-speed on-chip oscillator frequency is selected by bits 0 to 3 of option byte (000C2H/010C2H) and bits 0 to 2 of HOCODIV register.

2. This indicates the oscillator characteristics only. Refer to AC Characteristics for instruction execution time.



Items	Symbol	Conditions	MIN.	TYP.	MAX.	Unit	
Input voltage, VIH1 high VIH2 VIH2 VIH3 VIH4 VIH4	VIH1	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	·	0.8EV _{DD0}		EVDDO	V
	VIH2	P01, P03, P04, P10, P11, P13 to P17, P43, P44, P53 to P55,	TTL input buffer $4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$	2.2		EVDD0	V
		P80, P81, P142, P143	TTL input buffer $3.3 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}$	2.0		EVDD0	V
			TTL input buffer $2.4 \text{ V} \leq EV_{\text{DD0}} < 3.3 \text{ V}$	1.5		EVDDO	V
	VIH3	P20 to P27, P150 to P156	0.7V _{DD}		VDD	V	
	VIH4	P60 to P63	0.7EVDD0		6.0	V	
	VIH5	P121 to P124, P137, EXCLK, EXCL	0.8Vdd		VDD	V	
low	VIL1	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147		0		0.2EV _{DD0}	V
	VIL2	P01, P03, P04, P10, P11, P13 to P17, P43, P44, P53 to P55,	TTL input buffer 4.0 V \leq EV _{DD0} \leq 5.5 V	0		0.8	V
		P80, P81, P142, P143	TTL input buffer $3.3 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}$	0		0.5	V
			TTL input buffer 2.4 V \leq EV _{DD0} $<$ 3.3 V	0		0.32	V
	VIL3	P20 to P27, P150 to P156	0		0.3VDD	V	
	VIL4	P60 to P63	0		0.3EVDD0	V	
	VIL5	P121 to P124, P137, EXCLK, EXCLK	0		0.2VDD	V	

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$ (3/5)

- Caution The maximum value of V_{IH} of pins P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 is EV_{DD0}, even in the N-ch open-drain mode.
- **Remark** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply IDD2 current Note 2		HALT	HS (high- speed main) mode ^{Note 7}	$f_{IH} = 32 \text{ MHz}^{Note 4}$	V _{DD} = 5.0 V		0.62	3.40	mA
	Note 2	mode			V _{DD} = 3.0 V		0.62	3.40	mA
		mode	$f_{IH} = 24 \text{ MHz}^{Note 4}$	V _{DD} = 5.0 V		0.50	2.70	mA	
					V _{DD} = 3.0 V		0.50	2.70	mA
				fi⊢ = 16 MHz ^{Note 4}	V _{DD} = 5.0 V		0.44	1.90	mA
					V _{DD} = 3.0 V		0.44	1.90	mA
		HS (high- speed main) mode Note 7	$f_{MX} = 20 \text{ MHz}^{Note 3},$	Square wave input		0.31	2.10	mA	
			V _{DD} = 5.0 V	Resonator connection		0.48	2.20	mA	
				$f_{MX} = 20 \text{ MHz}^{Note 3},$	Square wave input		0.31	2.10	mA
			$V_{DD} = 3.0 V$	Resonator connection		0.48	2.20	mA	
				$f_{MX} = 10 \text{ MHz}^{Note 3},$	Square wave input		0.21	1.10	mA
			$V_{DD} = 5.0 V$	Resonator connection		0.28	1.20	mA	
				$f_{MX} = 10 \text{ MHz}^{Note 3},$	Square wave input		0.21	1.10	mA
	Subsystem	$V_{DD} = 3.0 V$	Resonator connection		0.28	1.20	mA		
		Subsystem clock operation	fsub = 32.768 kHz ^{Note 5}	Square wave input		0.28	0.61	μA	
			$T_A = -40^{\circ}C$	Resonator connection		0.47	0.80	μA	
				fsub = 32.768 kHz ^{Note 5}	Square wave input		0.34	0.61	μA
			T _A = +25°C	Resonator connection		0.53	0.80	μA	
				fsub = 32.768 kHz ^{Note 5}	Square wave input		0.41	2.30	μA
			$T_A = +50^{\circ}C$	Resonator connection		0.60	2.49	μA	
			fsub = 32.768 kHz ^{Note 5}	Square wave input		0.64	4.03	μA	
			$T_A = +70^{\circ}C$	Resonator connection		0.83	4.22	μA	
				$f_{SUB} = 32.768 \text{ kHz}^{Note 5}$	Square wave input		1.09	8.04	μA
				T _A = +85°C	Resonator connection		1.28	8.23	μA
			fsue = 32.768 kHz ^{Note 5}	Square wave input		5.50	41.00	μA	
				T _A = +105°C	Resonator connection		5.50	41.00	μA
		DD3 ^{Note 6} STOP mode ^{Note 8}	$T_A = -40^{\circ}C$				0.19	0.52	μA
			T _A = +25°C				0.25	0.52	μA
			T _A = +50°C				0.32	2.21	μA
			T _A = +70°C				0.55	3.94	μA
			T _A = +85°C				1.00	7.95	μA
			T _A = +105°C				5.00	40.00	μA

(2) Flash ROM: 96 to 256 KB of 30- to 100-pin products	
$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ V}_{DD1} \le 100 \text{ V}_{DD1} \le 1000 \text{ V}_{DD1} \le 100 \text{ V}_{DD1} = 100 $	$V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) (2/2)$

(Notes and Remarks are listed on the next page.)

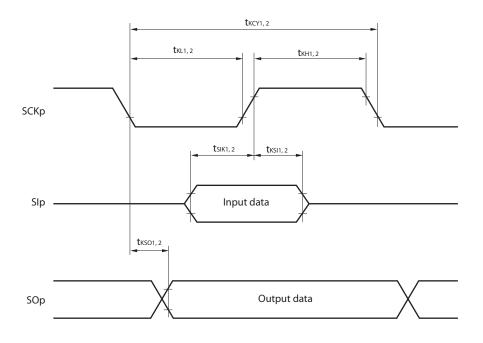


- **Notes 1.** Total current flowing into VDD, EVDDD, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDDD, and EVDD1, or Vss, EVSSD, and EVSS1. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. During HALT instruction execution by flash memory.
 - 3. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 4. When high-speed system clock and subsystem clock are stopped.
 - When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 - 6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - 7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

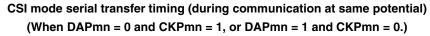
HS (high-speed main) mode: 2.7 V \leq V_DD \leq 5.5 V@1 MHz to 32 MHz 2.4 V \leq V_DD \leq 5.5 V@1 MHz to 16 MHz

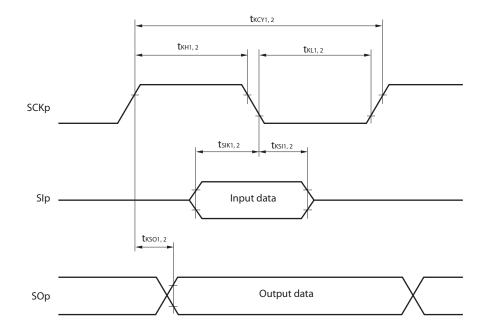
- 8. Regarding the value for current operate the subsystem clock in STOP mode, refer to that in HALT mode.
- **Remarks 1.** fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. file: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is $T_A = 25^{\circ}C$





CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



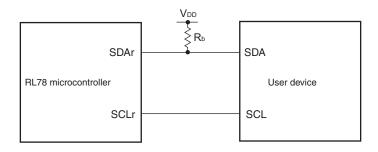


Remarks 1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31)

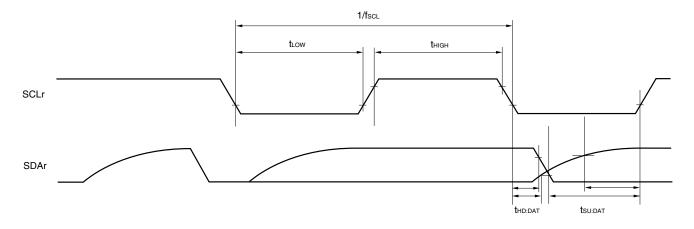
2. m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)



Simplified I²C mode mode connection diagram (during communication at same potential)



Simplified I²C mode serial transfer timing (during communication at same potential)



- **Remarks 1.** R_b[Ω]:Communication line (SDAr) pull-up resistance, C_b[F]: Communication line (SDAr, SCLr) load capacitance
 - r: IIC number (r = 00, 01, 10, 11, 20, 21, 30, 31), g: PIM number (g = 0, 1, 4, 5, 8, 14),
 h: POM number (g = 0, 1, 4, 5, 7 to 9, 14)
 - 3. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m

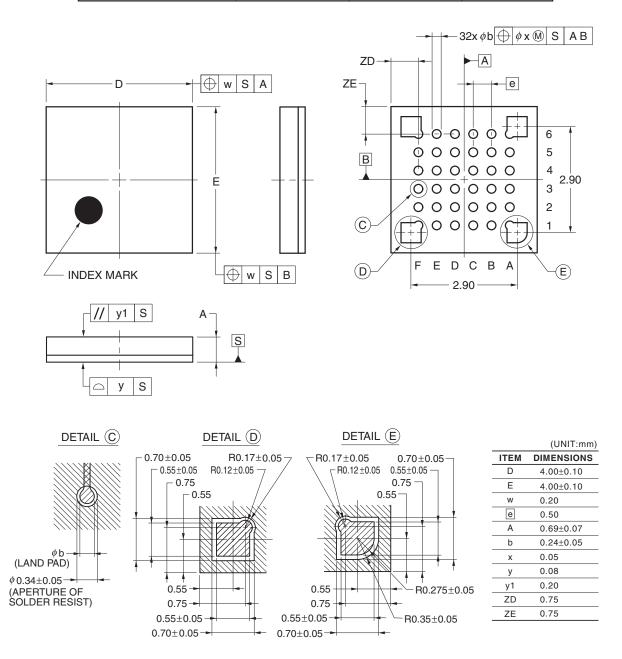
= 0, 1), n: Channel number (n = 0 to 3), mn = 00 to 03, 10 to 13)



4.6 36-pin Products

R5F100CAALA, R5F100CCALA, R5F100CDALA, R5F100CEALA, R5F100CFALA, R5F100CGALA R5F101CAALA, R5F101CCALA, R5F101CDALA, R5F101CEALA, R5F101CFALA, R5F101CGALA R5F100CAGLA, R5F100CCGLA, R5F100CDGLA, R5F100CEGLA, R5F100CFGLA, R5F100CGGLA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-WFLGA36-4x4-0.50	PWLG0036KA-A	P36FC-50-AA4-2	0.023



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4.9 48-pin Products

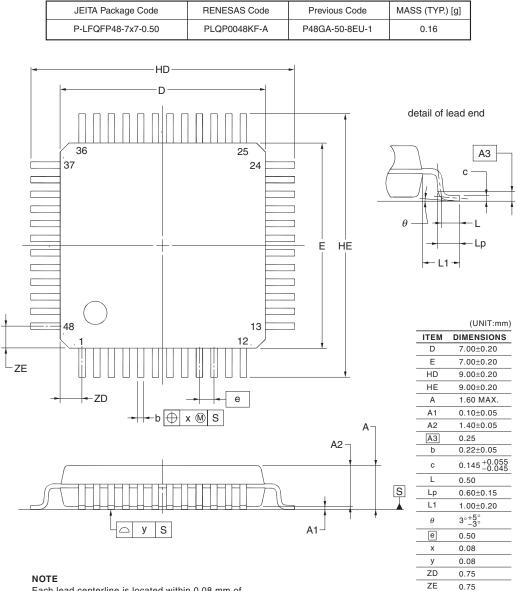
R5F100GAAFB, R5F100GCAFB, R5F100GDAFB, R5F100GEAFB, R5F100GFAFB, R5F100GGAFB, R5F100GHAFB, R5F100GJAFB, R5F100GKAFB, R5F100GLAFB

R5F101GAAFB, R5F101GCAFB, R5F101GDAFB, R5F101GEAFB, R5F101GFAFB, R5F101GGAFB, R5F101GHAFB, R5F101GJAFB, R5F101GKAFB, R5F101GLAFB

R5F100GADFB, R5F100GCDFB, R5F100GDDFB, R5F100GEDFB, R5F100GFDFB, R5F100GGDFB, R5F100GHDFB, R5F100GJDFB, R5F100GKDFB, R5F100GLDFB

R5F101GADFB, R5F101GCDFB, R5F101GDDFB, R5F101GEDFB, R5F101GFDFB, R5F101GGDFB, R5F101GHDFB, R5F101GJDFB, R5F101GKDFB, R5F101GLDFB

R5F100GAGFB, R5F100GCGFB, R5F100GDGFB, R5F100GEGFB, R5F100GFGFB, R5F100GGGFB, R5F100GHGFB, R5F100GJGFB



Each lead centerline is located within 0.08 mm of its true position at maximum material condition.

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